



Retraction Note to: A Review on Nanoporous Gallium Nitride (NPGaN) Formation on P-Type Silicon Substrate with the Mather-type Plasma Focus Device (MPFD)

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The Editor-in-Chief is retracting this article [1] because it has been previously published [2]. M. Habibi, who is listed as an author on the previous publication, is not listed as an author on this version. The authors have not responded to any correspondence from the publisher about this retraction.

[1] S. Sharifi Malvajerdi and A. Salar Elahi, A Review on Nanoporous Gallium Nitride Formation on P-type Silicon Substrate with the Mather-type Plasma Focus Device. *J. Inorg. Organomet. Polym.* 27(4), 948 (2017)

[2] S. Sharifi Malvajerdi, A. Salar Elahi, and M. Habibi. A novel technique based on a plasma focus device for nanoporous gallium nitride formation on P-type silicon. *Phys. Plasmas* 24, 043511 (2017)

The original article can be found online at <https://doi.org/10.1007/s10904-017-0541-9>.

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